

## **METHOD OF MANUFACTURING NON-VOLATILE DRAM**

### **ABSTRACT OF THE DISCLOSURE**

**[0072]** A method of forming a non-volatile DRAM includes, in part, forming a first polysilicon layer above a first dielectric layer to form a control gate of the non-volatile device disposed in the non-volatile DRAM, forming sidewall spacers adjacent the first polysilicon layer, forming a second polysilicon layer that forms a guiding gate of the non-volatile device disposed in the non-volatile DRAM and a gate of an MOS transistor disposed in the non-volatile DRAM, delivering first implants to the body region to form lightly doped areas in the body region, delivering second implants to the body region to define source and drain regions, forming second sidewall spacers above the body region to define regions receiving lightly doped implants and to define a conducting region of a capacitor disposed in the non-volatile DRAM.

60172754 v1